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BFQ149

PNP 5 GHz wideband transistor

Rev. 03 — 28 September 2007

Product data sheet

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NXP Semiconductors



NXP Semiconductors Product specification

PNP 5 GHz wideband transistor

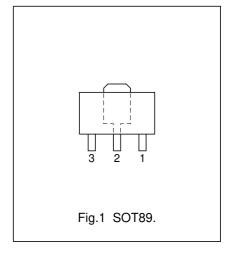
BFQ149

DESCRIPTION

PNP transistor in a SOT89 envelope. It is intended for use in UHF applications such as broadband aerial amplifiers (30 to 860 MHz) and in microwave amplifiers such as radar systems, spectrum analysers, etc., using SMD technology.

PINNING

PIN	DESCRIPTION		
Code: FG			
1	emitter		
2	collector		
3	base		



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	open base	_	_	-15	٧
I _C	DC collector current		_	_	-100	mA
P _{tot}	total power dissipation	up to T _s = 135 °C (note 1)	_	_	1	W
h _{FE}	DC current gain	$I_C = -70 \text{ mA}; V_{CE} = -10 \text{ V}; T_j = 25 \text{ °C}$	20	50	_	
f _T	transition frequency	$I_C = -75 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 500 MHz; T _j = 25 °C	4	5	_	GHz
G _{UM}	maximum unilateral power gain	$I_C = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ $f = 500 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	_	12	_	dB
F	noise figure	$I_{C} = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ $R_{s} = 60 \Omega; f = 500 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	_	3.75	_	dB

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-20	V
V _{CEO}	collector-emitter voltage	open base	_	-15	V
V _{EBO}	emitter-base voltage	open collector	_	-3	V
I _C	DC collector current		_	-100	mA
I _{CM}	peak collector current	f > 1 MHz	_	-150	mA
P _{tot}	total power dissipation	up to $T_s = 135$ °C (note 1)	_	1	W
T _{stg}	storage temperature		-65	150	°C
T _i	junction temperature		_	150	°C

Note

1. T_s is the temperature at the soldering point of the collector tab.

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THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
R _{th j-s}	thermal resistance from junction to soldering point	up to $T_s = 135$ °C (note 1)	40 K/W

Note

1. T_{s} is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -10 V;$	_	_	100	nA
h _{FE}	DC current gain	$I_C = -70 \text{ mA}; V_{CE} = -10 \text{ V}$	20	50	_	
f⊤	transition frequency	$I_{C} = -70 \text{ mA}; V_{CE} = -10 \text{ V};$ $f = 500 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	4	5	_	GHz
C _c	collector capacitance	I _E = 0; V _{CB} = -10 V; f = 1 MHz	_	2	_	pF
C _e	emitter capacitance	$I_C = 0$; $V_{EB} = -0.5 \text{ V}$; $f = 1 \text{ MHz}$	_	4	_	pF
C _{re}	feedback capacitance	$I_C = 0$; $V_{CE} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	1.7	_	pF
G _{UM}	maximum unilateral power gain (note 1)	$I_{C} = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ $f = 500 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	_	12	_	dB
F	noise figure	$I_{C} = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ $R_{s} = 60 \Omega; f = 500 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	_	3.75	_	dB

Note

1.
$$G_{UM}$$
 is the maximum unilateral power gain, assuming S_{12} is zero and
$$G_{UM} = 10 \log \frac{\left|S_{21}\right|^2}{\left(1-\left|S_{11}\right|^2\right)\left(1-\left|S_{22}\right|^2\right)} dB.$$

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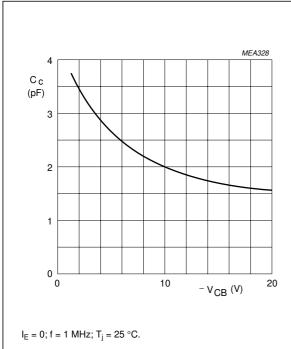
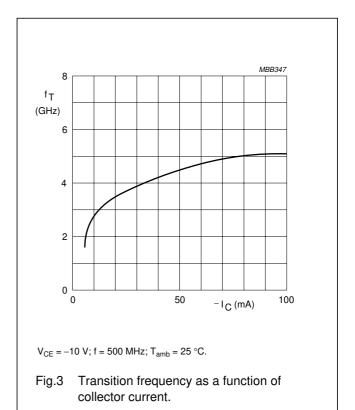
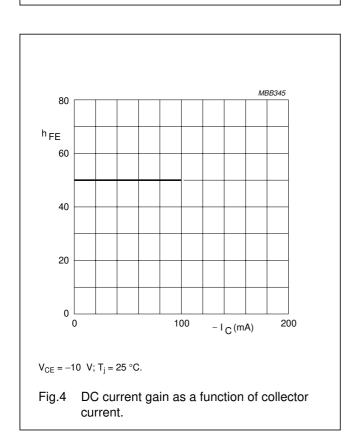
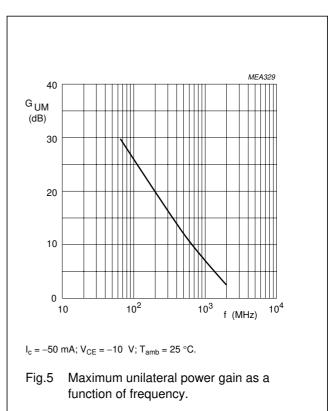


Fig.2 Collector capacitance as a function of collector-base voltage.







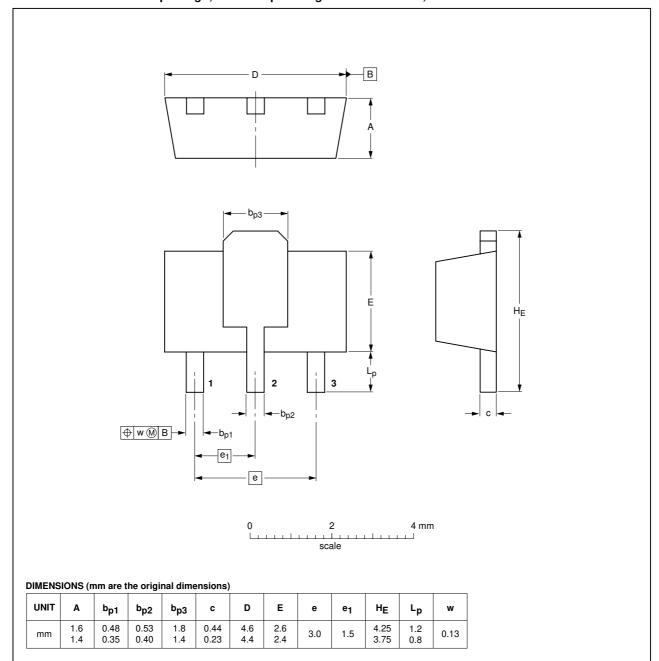
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PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE	UTLINE REFERENCES		EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT89		TO-243	SC-62			06-03-16 06-08-29	

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BFQ149 NXP Semiconductors

PNP 5 GHz wideband transistor

Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFQ149_N_3	20070928	Product data sheet	-	BFQ149_CNV_2
Modifications:	 Fig. 1 and p 	ackage outline updated		
BFQ149_CNV_2	19950901	Product specification	-	-

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